

Monday, April 3, 2017

	Ballroom I	Omega
08:00-08:30	Registration	
08:30-09:30	Leon Chua: Holy Grail of non-volatile memristors found!	
	Theory I Chair: A. Ascoli — TU Dresden, DE	Interfaces Chair: C. Papavassiliou — Imperial College London, UK
09:30-10:00	Keynote: A Note on the So-Called Inverse Memristor D. Biolek, V. Biolkova, Z. Kolka	Keynote: Influence of Interface Roughness on Resistance Switching in Undoped Amorphous Silicon Oxide A. Mehonic, M. Munde, W. Ng, M. Buckwell, L. Montesi, M. Bosman, A. Shluger, A. Kenyon
10:00-10:15	<i>Advanced Nonlinear Memristor Model with a Biolek Window Function and Voltage-Dependent Exponent</i> V. Mladenov, S. Kirilov	<i>Influence of counter electrode materials on redox processes and switching kinetics in electrochemical metallization cells</i> M. Lübben, S. Tappertzhoffen, S. Menzel, I. Valov
10:15-10:30	<i>Avoiding Discontinuities in Piecewise Linear Models for Memristor Oscillators</i> E. Ponce, J. Ros, E. Freire, A. Amador	<i>Demonstration of low power $TiO_{2-x}/HfO_{2-y}/TiO_{2-x}$-based RRAM devices with synaptic properties</i> P. Bousoulas, D. Tsoukalas
10:30-11:00	Coffee Break	
	Technology Chair: M. Ogorzałek — Jagiellonian University, PL	Materials and Devices Chair: D. Wouters — RWTH Aachen, DE
11:00-11:30	Keynote: Fabrication, CMOS integration and applications of non-volatile 3D metal oxide crossbars G. Adam, B. Chakrabarti, B. Hoskins, H. Nili, D. Strukov	Keynote: HfO_x-based memristive devices; from materials to applications S. Spiga, S. Brivio, E. Covi, J. Frascaroli
11:30-11:45	<i>Sub-15 nm High Density Crossbar Memristive Devices</i> A. Khiat, P. Ayliffe, T. Prodromakis	<i>Three-terminal $CeO_{2-x}/La_{0.8}Sr_{0.2}MnO_3$ device demonstrating volume resistive switching based on the metal to insulator transition</i> J. Sune, R. Ortega-Hernandez, M. Coll, J. Gonzalez-Rosillo, A. Palau, X. Obradors, J. Martin-Martinez, E. Miranda, T. Puig
11:45-12:00	<i>Memristive titanium, niobium and tantalum oxide films obtained by anodic oxidation</i> S. Noori, A. Brenna, F. Corinto, M. Pedferri, M. V. Diamanti	<i>Characterization and modelling of HfO_2-based devices showing second order memristor effects</i> A. Rodriguez-Fernandez, C. Cagli, L. Perniola, J. Sune, E. Miranda
12:00-12:15	<i>Tranmistor: A Device-Level Approach to Resolving the Sneak Currents of Crossbar Arrays</i> O. Bass, R. Giterman, A. Fish, D. Naveh	<i>I-V characteristics of nanowire based resistive change memory</i> T. Aono, K. Sugawa, T. Shimizu, S. Shingubara, K. Takase
12:15-12:30	<i>Impact of Volatile Switching Selector on ReRAM crossbar readout operations</i> S. Cortese, I. Messaris, A. Khiat, T. Prodromakis	<i>Resistance switching properties of silicon nitride material</i> P. Karakolis, A. Speliotis, V. Ioannou-Souglideris, P. Normand, P. Dimitrakis
12:30-13:30	Lunch	
13:30-14:30	Joshua Yang: Diffusive memristor for computing	
	Characterisation Chair: P. Dimitrakis — NCSR “Demokritos”, GR	Applications I Chair: F. Corinto — Politecnico di Torino, IT
14:30-15:00	Keynote: Effect of electrical measurement on the evolution of conductive filaments composed of oxygen vacancies in HfO_x-based ReRAM B. Attarimashalkoubeh, J. Sandrini, E. Shahrabi, Y. Leblebici	Keynote: Understanding and Engineering Memristors for Memory and Computing Applications Y. Yang
15:00-15:15	<i>Electrochemical and C-AFM characterization of anodic TiO_2 with memristive behaviour</i> S. Noori, T. Souier, M. Chiesa, M. Pedferri, M. V. Diamanti	<i>Implementation of fuzzy-type logic learning with bidirectional, $BiFeO_3$-based artificial synapses</i> H. Schmidt, N. Du, M. Kiani, D. Bürger, I. Skoru, R. Ecke, M. Di Ventra, O. G. Schmidt, S. E. Schulz
15:15-15:30	<i>Bipolar Resistive Switching Analysis in $Au/TiO_{2-x}/TiO_2/Au$ Memristor structure Employing Ex-situ Impedance Spectroscopy</i> C. Dash, S. Sahoo, S.R.S Prabaharan	<i>Memristive Current Mode Threshold Logic Gates</i> S. N. Mozaffari, S. Tragoudas
15:30-17:30	POSTER SESSION I Materials and Devices	MemoCIS Management Committee Meeting

Tuesday, April 4, 2017

	Ballroom I	Omega
08:30-09:30	Ilia Valov: Mechanisms in memristive switching: fundamental processes and limitations	
	Reliability Chair: A. Kenyon — University College London, UK	Theory II Chair: D. Bielek — Brno University, CZ
09:30-10:00	Keynote: Reliability issues on oxide-electrolyte-based RRAM M. Liu, Q. Liu, S. Liu, X. Zhao, H. Lv, S. Long	Keynote: Vacancy Transport Unites Memristor Models I. Abraham
10:00-10:15	<i>Correlation analysis between V set, V reset, V forming, LRS and HRS in oxide-based ReRAMs</i> J. Sandrini, E. Shahrabi, B. Attarimashalkoubeh, Y. Leblebici	<i>Role of electron and hole injection in electroforming of SiO₂ and HfO₂ based RRAM cells</i> D. Gao, J. Strand, A. Mehonic, A. Kenyon, A. Shluger
10:15-10:30	<i>Highly reliable and flexible memristive device fabricated by all printed approach with an advanced 2D nanocomposite as the functional material</i> M. M. Rehman, Y. J. Yang, S. W. Kim, K. H. Choi	<i>A compact Verilog-A ReRAM model</i> I. Messaris, A. Serb, A. Khiat, S. Nikolaidis, T. Prodromakis
10:30-11:00	Coffee Break	
	Bioinspired Sensors Chair: S. Carrara — EPFL, CH	Logic Chair: D. Ielmini — Politecnico di Milano, IT
11:00-11:30	Keynote: Wiring brain and artificial neurons together through memristive synapses: the first steps S. Vassanelli	Keynote: Influence of ReRAM Device Characteristics on the Performance of Logic-in-Memory Concepts A. Siemon, L. Xie, S. Menzel, R. Waser, S. Hamdioui, D. Wouters
11:30-11:45	<i>Memristor-based Spike Sorting platform</i> I. Gupta, A. Serb, A. Khiat, T. Prodromakis	<i>Functional complete Boolean logic methodology in memristors with optimized computation complexity</i> Y. Li, Y. Zhou, Z. Wang, L. Cheng, X. Miao
11:45-12:00	<i>Neuromorphic Device Architectures using Electrolyte Gating</i> P. Gkoupidenis, D. Koutsouras, G. Malliaras	<i>Transient Analysis of an Experimentally-Verified Memristor-Based IMPLY Gate</i> M. Maestro, J. Martin-Martinez, A. Crespo-Yepes, M. Escudero, R. Rodriguez, M. Nafria, X. Aymerich, A. Rubio
12:00-12:15	<i>Energy and Area Efficient Image Compressor using Memristive Crossbar</i> Y. Halawani, B. Mohammad, M. Al-Qutayri, S. Al-Sarawi	<i>mMPU: Memristive Memory Processing Unit</i> S. Kvatinsky, R. Ben-Hur, N. Talati, N. Wald
12:15-12:30	<i>Neuromorphic Pattern Recognition Based on Bi-directional Analog Switching ReRAM Array</i> P. Yao, H. Wu, B. Gao, H. Qian	<i>Memristive Probabilistic Arithmetic Unit</i> H. Alahmadi, R. Naous, K. Nabil Salama
12:30-13:30	Lunch	
13:30-14:30	Daniele Ielmini: Neuromorphic hardware for pattern learning with memristive synapses	
	Circuits and Control Chair: J. Georgiou — Univ. of Cyprus, CY	Devices and Applications Chair: D. Querlioz — Univ. Paris-Sud, FR
14:30-15:00	Keynote: On the use of offset calibration techniques for low-power memristor arrays read-out C. Mohan, J.M. de la Rosa, T. Serrano-Gotarredona, B. Linares-Barranco	Keynote: “Tug of War” devices for interconnection of artificial synapses C. Lutz, T. Hasegawa, T. Chikyow
15:00-15:15	<i>Memristor-based control methods for a bio-inspired robot</i> R. Tetzlaff, A. Ascoli, D. Baumann, M. Hild	<i>Pt/TiO_x/Pt Resistive switching devices for flexible applications</i> A. Khiat, S. Cortese, A. Serb, T. Prodromakis
15:15-15:30	<i>Memristive-based Reconfigurable Analogue Blocks</i> C.A. Angeles Ruiz, A. Serb, A. Khiat, C. Papavassiliou, T. Prodromakis	<i>How Mott insulator can implement a single component Leaky Integrate and Fire artificial neuron</i> C. Adda, P. Stoliar, J. Tranchant, B. Corraze, M. P. Besland, M. Rozenberg, E. Janod, L. Cario
15:30-17:30	POSTER SESSION II Theory and Applications	MemoCIS Working Group Meeting

Wednesday, April 5, 2017

	Ballroom I	Omega
09:00-10:00	Giacomo Indiveri: Distributed heterogeneous memory structures in multi-core neuromorphic computing architectures	
	Applications II Chair: G. Sirakoulis — Democritus Univ. Thrace, GR	Memristor-based Sensors Chair: S. Vassanelli — Univ. of Padova, IT
10:00-10:30	Keynote: Computational memory based on phase-change memory devices A. Sebastian	Keynote: Memristive Aptasensors for Theranostics I. Tzouvadaki, N. Aliakbarinodehi, G. de Micheli, S. Carrara
10:30-10:45	<i>Tuning individual and mutually synchronized spin Hall nanooscillators for associative memory neural networks</i> M. Zahedinejad, A. Awad, A. Houshang, J. Åkerman	<i>Fabrication of Fluidic-based Memristor Sensor for Dengue Virus Detection</i> N. S. M. Hadis, A.A. Manaf, S.H. Ngalm, S.H. Herman
10:45-11:00	<i>Processing with Memristors for Approximate and Stochastic Computing</i> R. Naous, K.N. Salama	<i>Low-Power and Highly Stable Microscale TiO₂ Memristor for Gamma-Ray Sensing</i> L. Mahmoud, M.A. Jaoude, M. Darweesh, H. Abunahla, G. Hitt, B. Mohammad
11:00-11:30	Coffee Break	
	Neuromorphic Computation Chair: B. Linares-Barranco — CSIC/Univ. of Seville, ES	Non-Volatile Memories Chair: I. Valov — Forschungszentrum Jülich, DE
11:30-12:00	Keynote: “Winner-Take-All” Neuromorphic Architectures with Phase-Change Synapses S. Sidler, S. Wozniak, Y. Leblebici, A. Pantazi, E. Eleftheriou	Keynote: Memristor-Based Circuit Designs: From Nonvolatile Logics to Neuromorphic Computing Systems M.F. Chang, W.H. Chen, W.S. Khwa, K.T. Tang, C.C. Hsieh, M.S. Ho
12:00-12:15	<i>Unsupervised learning in probabilistic neural networks with multi-state MOx memristive synapses</i> A. Serb, J. Bill, A. Khiat, R. Berdan, R. Legenstein, T. Prodromakis	<i>Multilevel Resistive Switching Effect in Bilayer Structures Pt/TiO₂/Al₂O₃/Pt</i> L. Alekseeva, T. Nabatame, T. Chikyow, A. Petrov
12:15-12:30	<i>Full-hardware demonstration of unsupervised learning in ReRAM synaptic networks</i> D. Ielmini, G. Pedretti, V. Milo, R. Carboni, S. Bianchi, S. Ambrogio	<i>The use of dielectric barrier layers for multibit operation in TiO_x-based memristors</i> S. Stathopoulos, A. Khiat, M. Trapatseli, S. Cortese, A. Serb, T. Prodromakis
12:30-12:45	<i>Stochastic training and the impact of noise in memristive neuromorphic hardware</i> G. Pedretti, V. Milo, R. Carboni, S. Bianchi, S. Ambrogio, D. Ielmini	<i>Investigation of the Multilevel Capability of TiN/Ti/HfO₂/W RRAM Devices by Pulse Programming</i> M. B. Gonzalez, S. Poblador, M. Muñoz-Mallol, J. Calvo, M. Zabala, M. C. Acero, F. Campabadal
12:45-13:00	<i>Double-layer perceptron based on memristive effect in metal-oxide nanostructures</i> A. Mikhaylov, O. Morozov, P. Ovchinnikov, I. Antonov, A. Belov, D. Korolev, M. Koryazhkina, E. Gryaznov, O. Gorshkov, V. Kazantsev	<i>TaO_x based resistive switching memory with Al₂O₃ interfacial layer in W/Al₂O₃/TaO_x/TiN structure and evolution of switching mechanism</i> S. Chakrabarti, S. Ginnaram, A. Roy, K. Singh, S. Jana, J.T. Qiu, S. Maikap
13:00-14:00	Lunch	
14:00-15:00	Wei Lu: Memristive devices for computing	
	Neurosynaptic Dynamics Chair: G. Indiveri — ETH Zürich, CH	Integration Chair: D. Tsoukalas — Nat. Tech. Univ. Athens, GR
15:00-15:30	Keynote: Exploiting the Intrinsic Spike Timing Dependent Plasticity Effects of Electro-Chemical Metallization Cells for Low-Overhead Learning A.F. Vincent, S. La Barbera, D. Vuillaume, F. Alibart, D. Querlioz	Keynote: Advances in 3D heterogeneous integration M. Ogorzalek
15:30-15:45	<i>Emulating neurological and psychological functions with ionic/electronic conducting titanates</i> X. Guo	<i>Toward chip-Level ReRAMs-CMOS Co-Integration</i> E. Shahrabi, J. Sandrini, B. Attarimashalkoubek, Y. Leblebici
15:45-16:00	<i>Synaptic Plasticity implemented in TiN/HfO₂/W structures</i> J. Martin-Martinez, N. Jimenez, M. Pedro, M.B. Gonzalez, R. Rodriguez, M. Nafria, F. Campabadal	<i>Inkjet-printed resistive memory cells for transparent electronics</i> B. Huber, J. Schober, M. Hange, S. Pschierer, M. Kaiser, A. Ruediger, C. Schindler

Thursday, April 6, 2017

Memristor Technologies open issues and the near future Ballroom I	
09:00-09:15	<i>Introduction</i> P. Dimitrakis (Institute of Nanoscience & Nanotechnology, NCSR “Demokritos”)
09:15-09:30	<i>Technology and Processing</i> R. Yakov (Towerjazz Inc.)
09:30-09:45	<i>Devices</i> A. Regev (Weebit-nano)
09:45-10:00	<i>Applications</i> A. Sebastian (IBM)
10:00-10:15	<i>Tools</i> R. Berdan (ArC Instruments)
10:15-10:30	<i>Embedded Applications</i> W. Lu (Crossbar Inc.)
10:30-11:00	Coffee Break
11:00-13:00	Panel discussion
13:00-14:00	Lunch